

16Mb Burst CellularRAM™ 1.0 Memory Automotive Temperature Addendum

MT45W1MW16BDGB-708 AT

Features

- Single device supports asynchronous, page, and burst operations
- VCC, VCCQ voltages
 - 1.7–1.95V VCC
 - 1.7–3.6V VCCQ
- Random access time: 70ns
- Burst mode READ and WRITE access
 - 4, 8, or 16 words, or continuous burst
 - Burst wrap or sequential
 - MAX clock rate: 80 MHz ($t_{CLK} = 12.5ns$)
 - Burst initial latency: 50ns (4 clocks) @ 80 MHz
 - t_{ACLK} : 9ns @ 80 MHz
- Page mode read access
 - Sixteen-word page size
 - Interpage read access: 70ns
 - Intrapage read access: 20ns
- Low power consumption
 - Asynchronous READ: <20mA
 - Intrapage read: <15mA
 - Initial access, burst READ: (50ns [4 clocks] @ 80 MHz) < 30mA
 - Continuous burst READ: <28mA
 - Standby: <70µA
 - Deep power-down: <3µA (TYP at 25°C)
- Low-power features
 - On-chip, temperature-compensated refresh (TCR)
 - Partial-array refresh (PAR)
 - Deep power-down (DPD) mode

Options

- Configuration:
 - 1 Meg x 16
 - VCC core voltage supply: 1.8V
 - VCCQ I/O voltage supply: 1.8V
- Package: 54-ball VFPGA (green)
- Timing: 70ns access
- Frequency: 80 MHz
- Standby power: Standard
- Operating temperature range: Automotive (–40°C to +105°C)

Designator

MT45W1MW16BD
GB
–70
8
None
AT

Part Number Example:

MT45W1MW16BDGB-708 AT

Full Data Sheet Compliance for All Parameters

For MT45W1MW16BDGB-708 AT devices, all timing and DC parameter values for the automotive temperature range (-40°C to $+105^{\circ}\text{C}$) remain the same as the standard data sheet values.



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This data sheet contains minimum and maximum limits specified over the power supply and temperature range set forth herein. Although considered final, these specifications are subject to change, as further product development and data characterization sometimes occur.